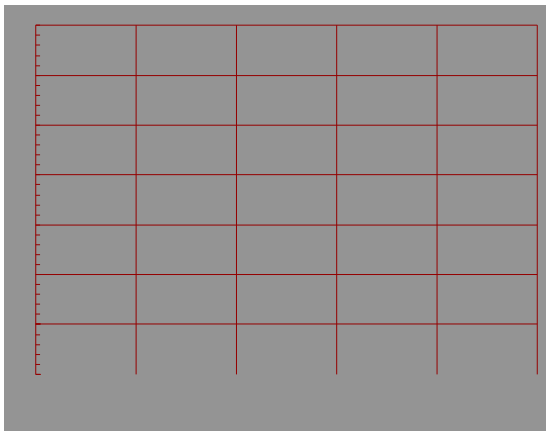
| | | | |
|---|---|---|---|
| Peak gate current ($t_p$=20μs , $T_j$=125 ) | $I_{GM}$ | 10 | A |
| Average gate power dissipation ($T_j$=125 ) | $P_{G(AV)}$ | 1 | W |
| Peak gate power | $P_{GM}$ | 20 | W |
| Peak pulse voltage ($T_j$=25 ; non-repetitive,off-state;FIG.7) | $V_{pp}$ | 0.5 | kV |

**ELECTRICAL CHARACTERISTICS** ($T_j$=25 unless otherwise specified)

| | | |
|---|---|---|
| | | |

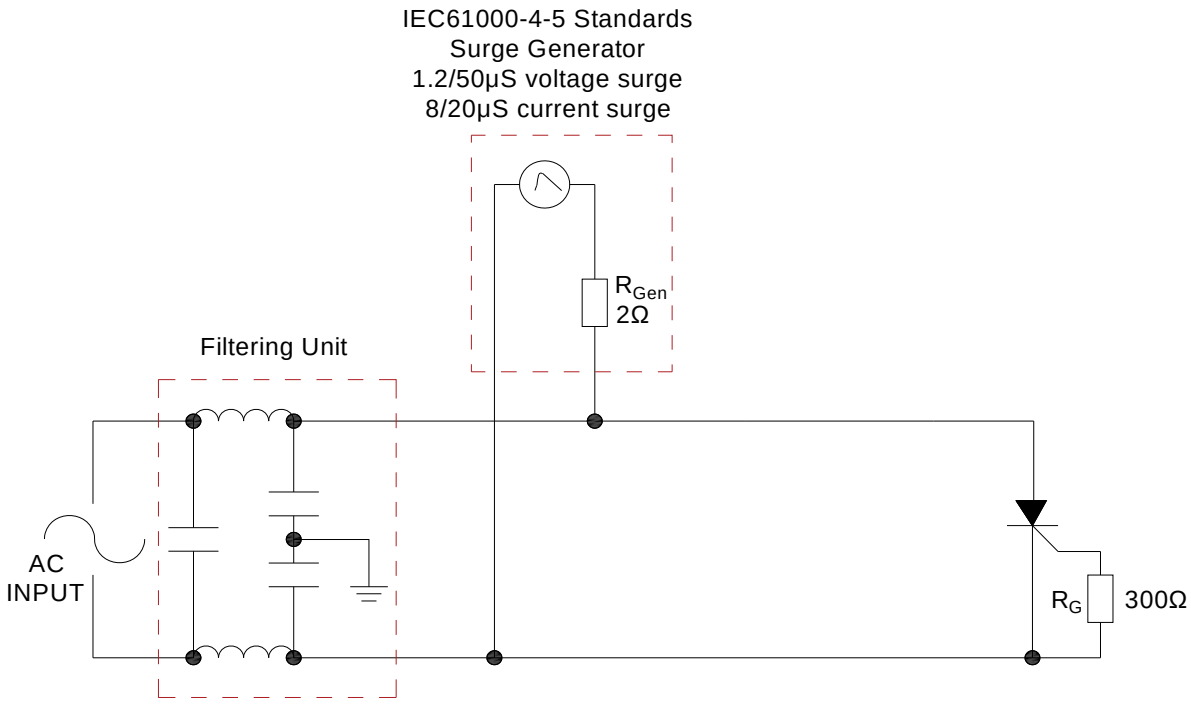


Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.




## LEAD FORMING AND SOLDERING

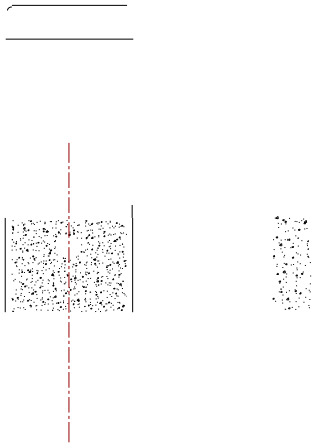
Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

## ORDERING INFORMATION

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|---|---|---|---|---|---|
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| Date | Revision | Changes |
|---|---|---|
| Apr.13, 2023 | A.1.0 | Last update |
| Oct.15, 2025 | A.1.1 | Revise PACKAGE MECHANICAL DATA |

## PACKAGE MECHANICAL DATA



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